



**Advanced Power
Electronics Corp.**

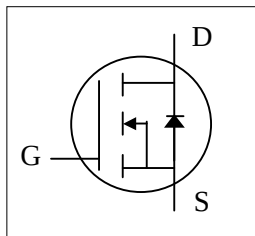
AP04N80I-HF

Halogen-Free Product

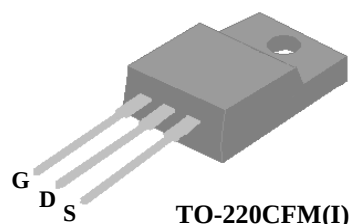
N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ 100% Avalanche Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant



BV_{DSS}	800V
$R_{DS(ON)}$	4.5Ω
I_D	3.2A



TO-220CFM(I)

Description

AP04N80 series are specially designed as main switching devices for universal 90 ~ 265VAC off-line AC/DC converter applications.

TO-220CFM type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.2	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	1.7	A
I_{DM}	Pulsed Drain Current ¹	12	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	34.7	W
E_{AS}	Single Pulse Avalanche Energy ³	4.5	mJ
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	3.6	$^\circ\text{C}/\text{W}$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient	65	$^\circ\text{C}/\text{W}$



Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	800	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =1A	-	-	4.5	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	4	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =1A	-	2	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =640V, V _{GS} =0V	-	-	100	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±30V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =1A	-	18	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	3.8	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	6	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =300V	-	15	-	ns
t _r	Rise Time	I _D =1A	-	20	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =50Ω	-	105	-	ns
t _f	Fall Time	V _{GS} =10V	-	30	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	800	1280	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	55	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	4	-	pF
R _g	Gate Resistance	f=1.0MHz	-	3.6	7.2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1.2A, V _{GS} =0V	-	-	1.5	V
t _{rr}	Reverse Recovery Time	I _S =1A, V _{GS} =0V	-	320	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	1.3	-	μC

Notes:

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test
- 3.Starting T_j=25°C , V_{DD}=50V , L=1mH , R_G=25Ω , I_{AS}=3A

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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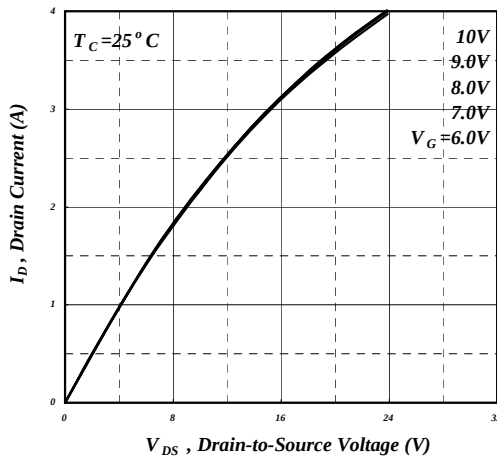


Fig 1. Typical Output Characteristics

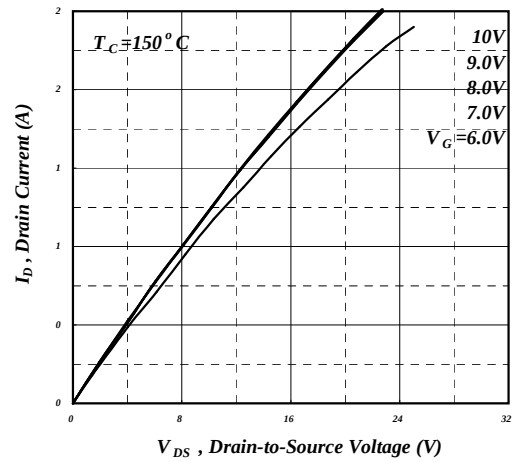


Fig 2. Typical Output Characteristics

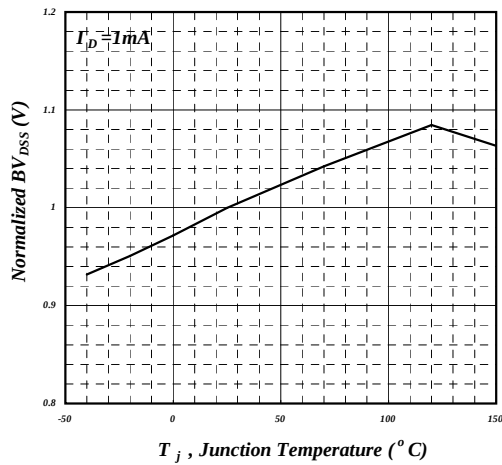


Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

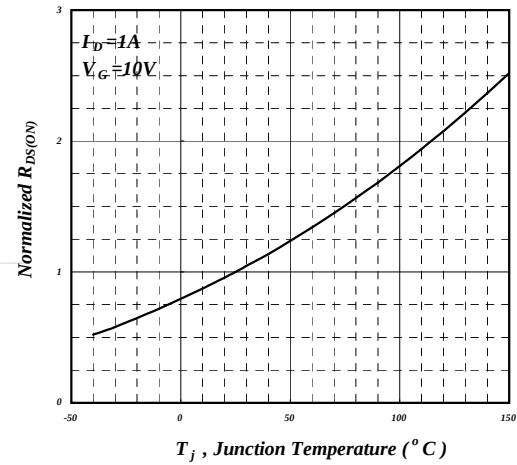


Fig 4. Normalized On-Resistance v.s. Junction Temperature

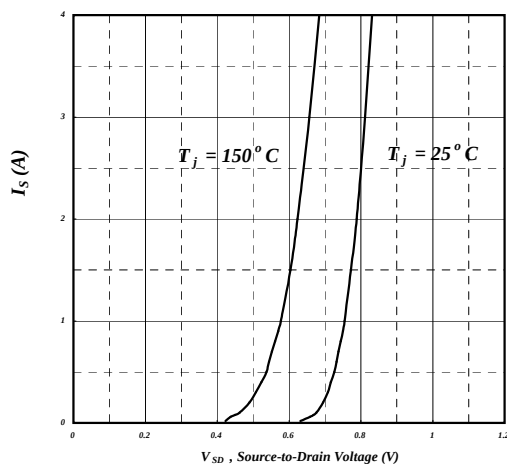


Fig 5. Forward Characteristic of Reverse Diode

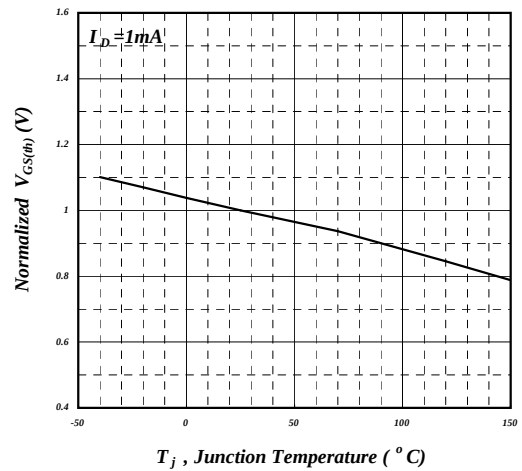


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

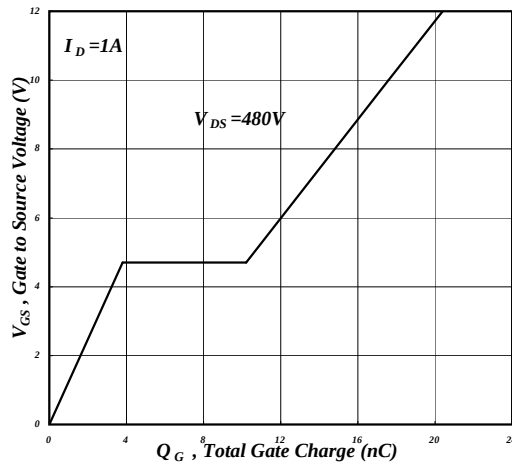


Fig 7. Gate Charge Characteristics

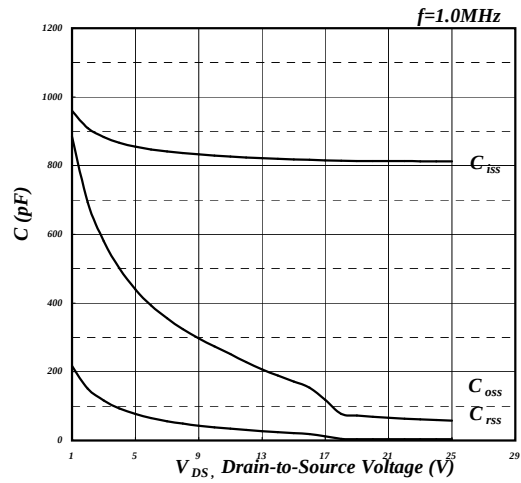


Fig 8. Typical Capacitance Characteristics

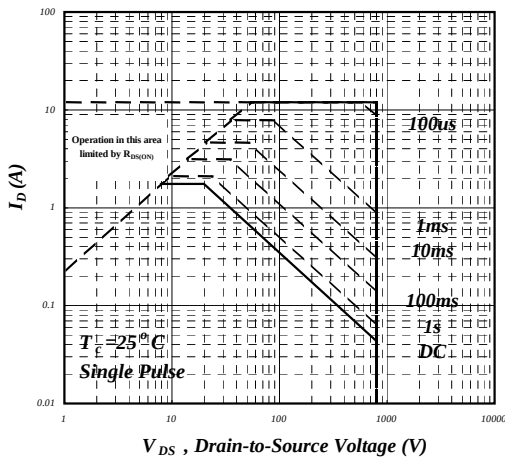


Fig 9. Maximum Safe Operating Area

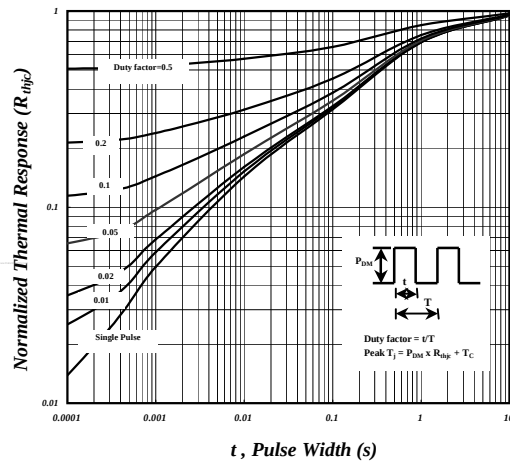


Fig 10. Effective Transient Thermal Impedance

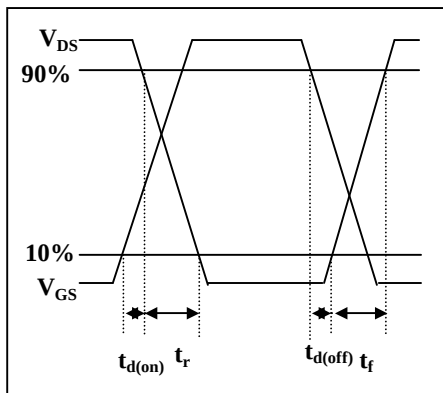


Fig 11. Switching Time Waveform

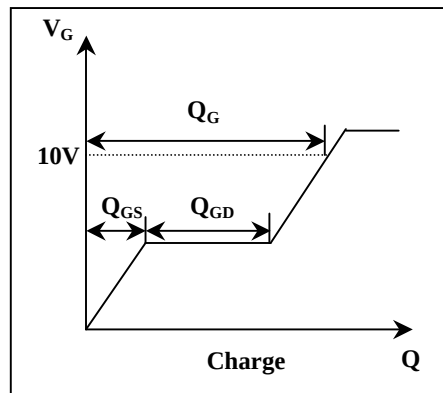


Fig 12. Gate Charge Waveform